ROITHNER LASERTECHNIK

A-1040 WIEN, FLEISCHMANNGASSE 9
TEL: +43 -1- 586 52 43 FAX: +43 -1- 586 41 43
e-mail: rlt@mcb.at http://www.roithner.mcb.at

PRELIMINARY

S808250G TECHNICAL DATA

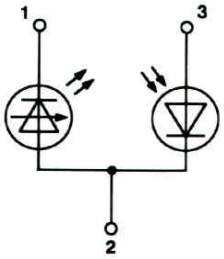
High Power Infrared Laserdiode

Structure: **InGaAs**
Lasing wavelength: **808 nm typ.**
Output power: **250 mW, cw**
Package: **9 mm**

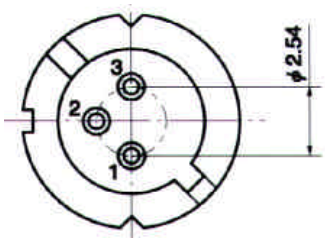
NOTE!
LASERDIODE
MUST BE COOLED!

ATTENTION
OBSERVE PRECAUTIONS FOR HANDLING
ELECTROSTATIC SENSITIVE DEVICE

PIN CONNECTION:



1) Laser diode cathode
2) Laser diode anode and photodiode cathode
3) Photodiode anode



Absolute Maximum Ratings (Tc = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P_o	250	mW
LD Reverse Voltage	$V_{R(LD)}$	2	V
PD Reverse Voltage	$V_{R(PD)}$	30	V
Operating Temperature	T_C	-10 .. +40	°C
Storage Temperature	T_{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P_o	kink free		200	250	mW
Threshold Current	I_{th}			160	200	mA
Operation Current	I_{op}	P_o = 250 mW		450	500	mA
Operation Voltage	V_{op}	P_o = 250 mW		1.8	2.1	V
Slope Efficiency	η		0.8	0.9	1.2	W/A
Lasing Wavelength	λ	P_o = 250 mW	803	808	812	nm
Beam Divergence	$\theta_{//}$	P_o = 250 mW	6	8	10	°
Beam Divergence	$\theta_{\perp}$	P_o = 250 mW	27	29	31	°
Lasing Aperture	A	P_o = 250 mW		50x1		µm²
Monitor Current	I_m	P_o = 250 mW	1.5	4.0	7.0	mA